AP30H10NF

100V N-Channel Enhancement Mode MOSFET

Description

The AP30H10NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 100V I_D =30A

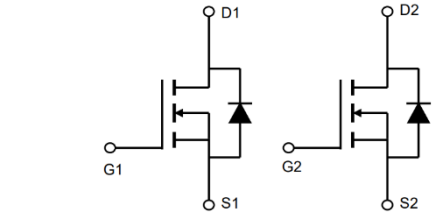
$R_{DS(ON)}$ < 45mΩ@ V_{GS}=10V **(Type：36mΩ)**

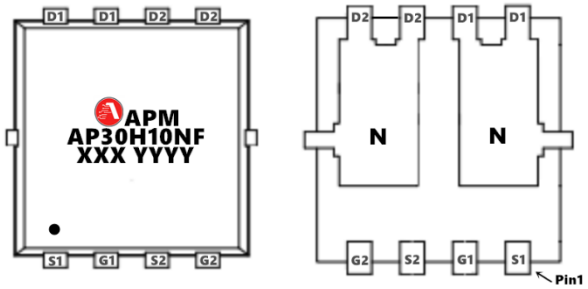
Application

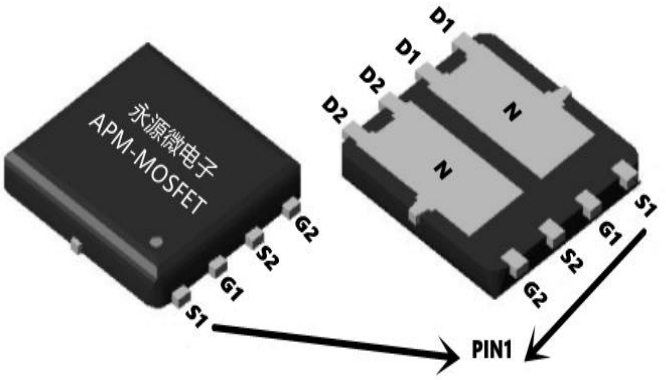
Automative lighting

Load switch

Uninterruptible power supply







Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP30N10NF	PDFN5*6-8L	AP30N10NF XXX YYYY	5000

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Drain Current, V_{GS} @ 10V	30	A
I_D@T_C=100℃	Drain Current, V_{GS} @ 10V	13	A
IDM	Pulsed Drain Current[1]	90	A
P_D@T_C=25℃	Total Power Dissipation	42	W
P_D@T_A=25℃	Total Power Dissipation[3]	1.7	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
RθJA	Maximum Thermal Resistance, Junctionambient	25	℃/W
RθJC	Maximum Thermal Resistance, Junction-case	3.6	℃/W

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Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	107	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.2	V
RDS(on)	Static Drain-Source on-Resistance	V_{GS}=10V, I_D=10A	-	36	48	mΩ
		V_{GS}=4.5V, I_D=6A	-	39	55	mΩ
Ciss	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	1964	-	pF
Coss	Output Capacitance		-	90	-	pF
Crss	Reverse Transfer Capacitance		-	74	-	pF
Q_g	Total Gate Charge	V_{DS}=80V, I_D=20A, V_{GS}=4.5V	-	20	-	nC
Qgs	Gate-Source Charge		-	3.1	-	nC
Qgd	Gate-Drain(“Miller”) Charge		-	14	-	nC
td(on)	Turn-on Delay Time	V_{DS}=80V, I_D=20A, R_G=3.1Ω, V_{GS}=4.5V	-	11	-	ns
tr	Turn-on Rise Time		-	91	-	ns
td(off)	Turn-off Delay Time		-	40	-	ns
t_f	Turn-off Fall Time		-	71	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	30	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	A
VSD	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=20A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=100A/μs	-	64	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	152	-	nC

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The EAS data shows Max. rating . The test condition is VDD=72V,VGS=10V,L=0.1mH,IAS=10A

4、The power dissipation is limited by 150℃ junction temperature

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

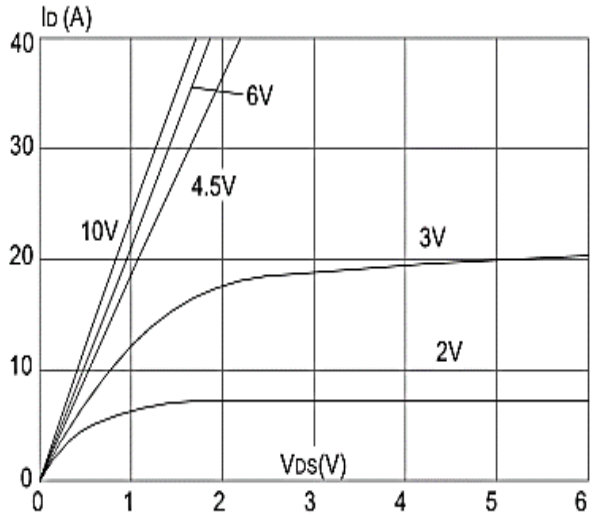

Figure1: Output Characteristics

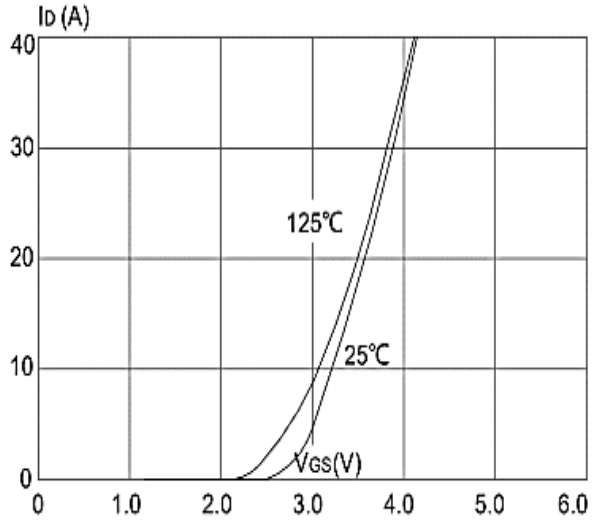

Figure 2: Typical Transfer Characteristics

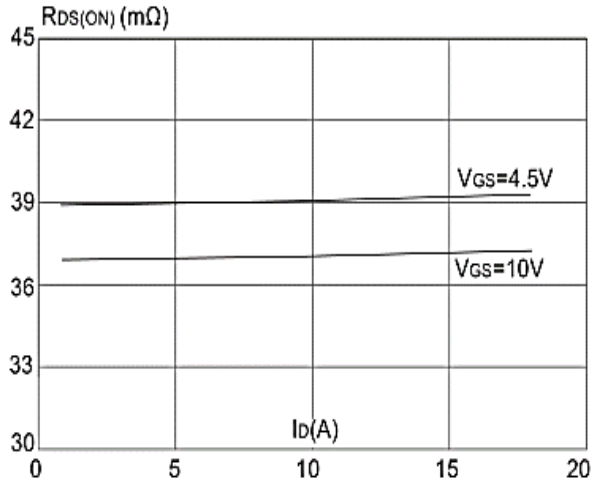

Figure 3:On-resistance vs. Drain Current

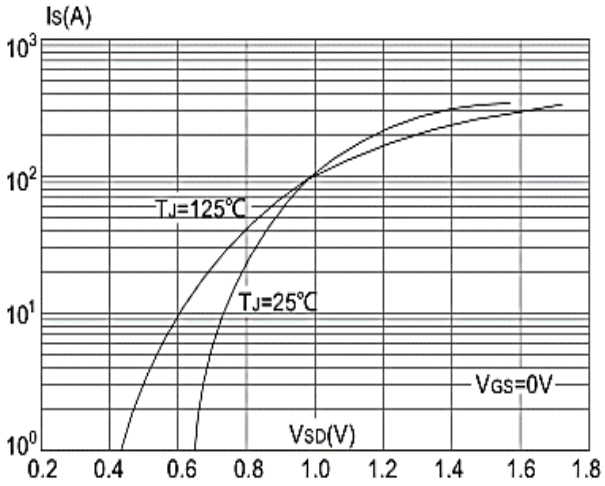

Figure 4: Body Diode Characteristics

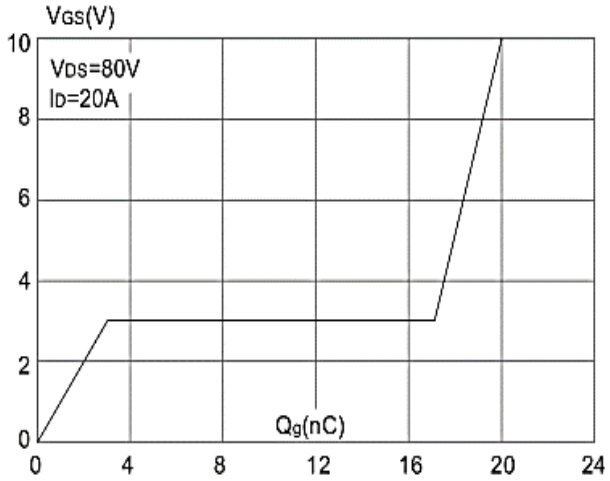

Figure 5: Gate Charge Characteristics

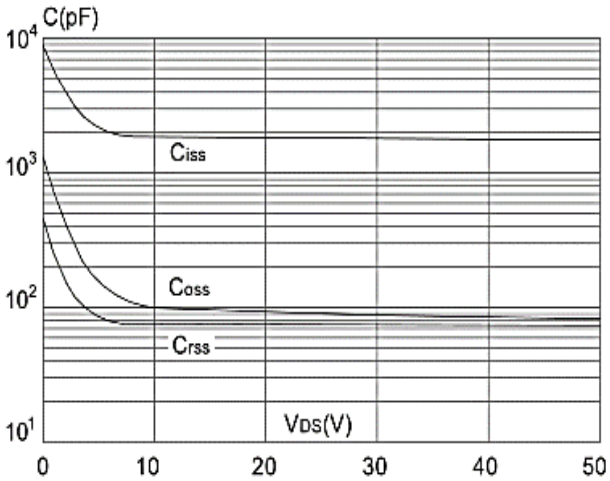

Figure 6: Capacitance Characteristics

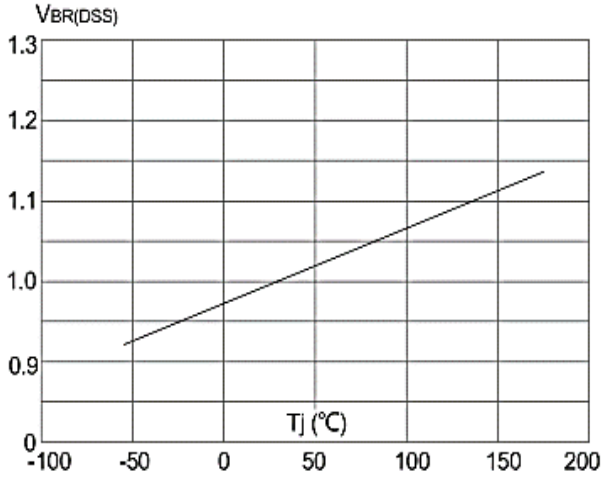

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

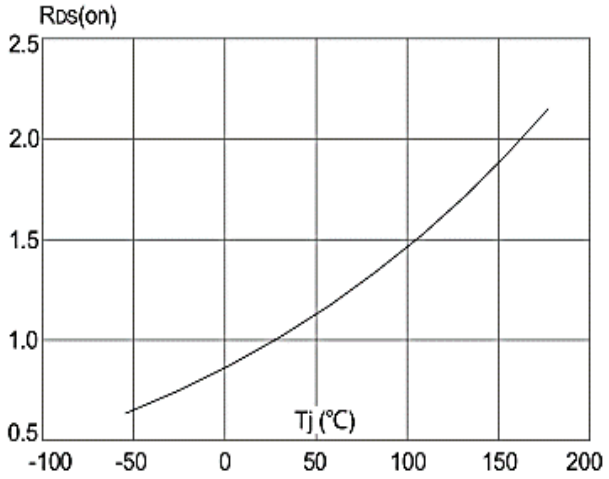

Figure 8: Normalized on Resistance vs Junction Temperature

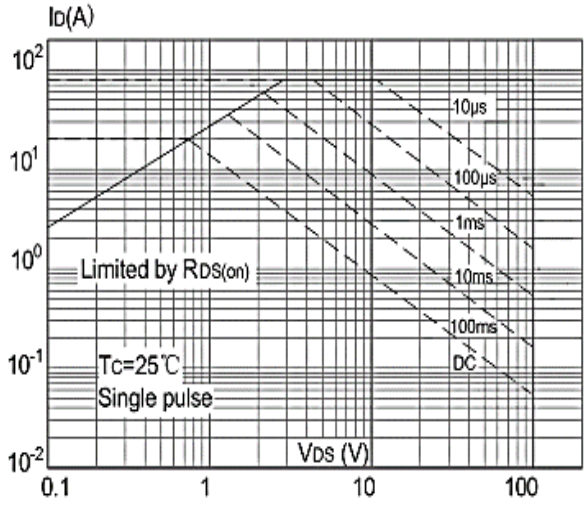

Figure 9: Maximum Safe Operating Area vs. Case Temperature

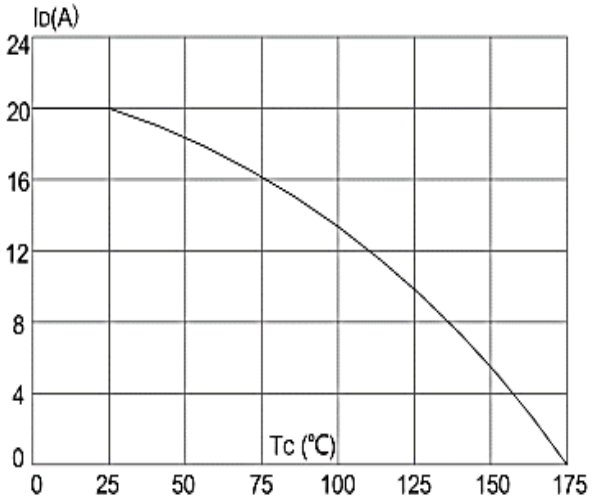

Figure 10: Maximum Continuous Drain Current

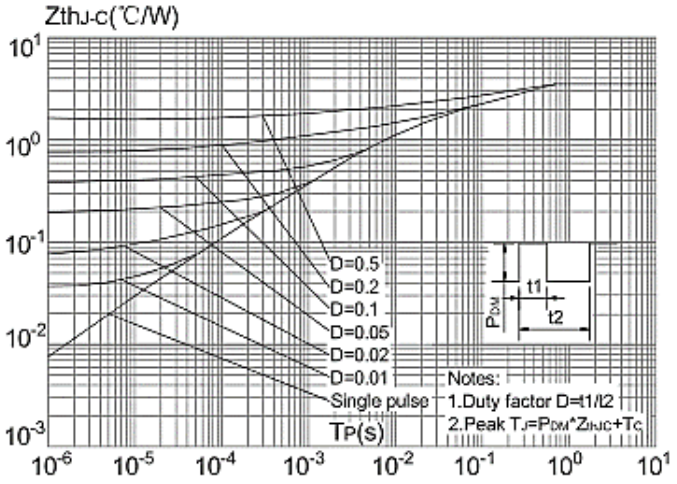

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

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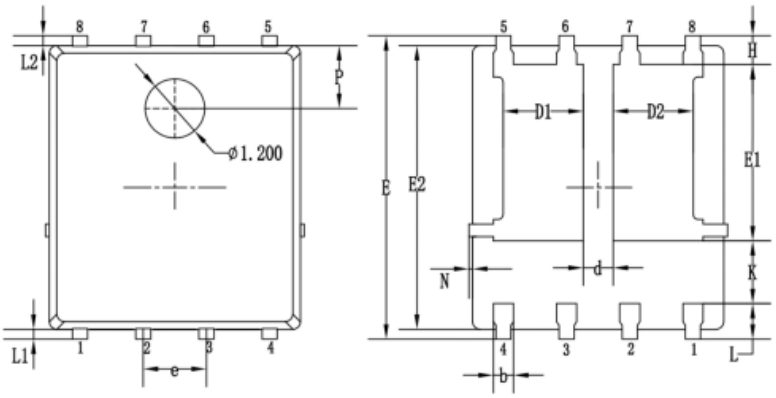
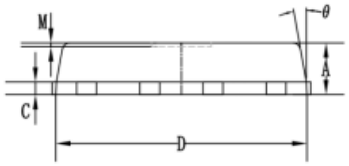
Package Mechanical Data-PDFN5X6-8L





Symbol	Dim in mm		
	min	typ	max
A	0.9	1.05	1.2
b	0.3	0.4	0.5
C	0.2	0.25	0.35
D	4.9	5.05	5.2
D1/D2	1.51	1.66	1.81
E	5.9	6.1	6.3
E1	3.3	3.5	3.7
E2	5.6	5.75	5.9
e	1.27BSC		
H	0.48	0.58	0.7
K	1.14	1.27	1.4
L	0.54	0.74	0.84
L1/L2	0.1	0.2	0.3
θ	8°	10°	12°
M	0.08REF		
N	0		0.15
P	1.28REF		
d	0.5	0.6	0.7

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Edition	Date	Change
REV1.0	2024/3/29	Initial release